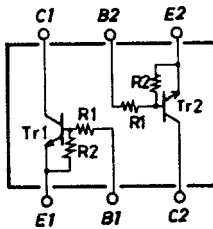


SANYO**FC110**

NPN Epitaxial Planar Silicon Composite Transistor

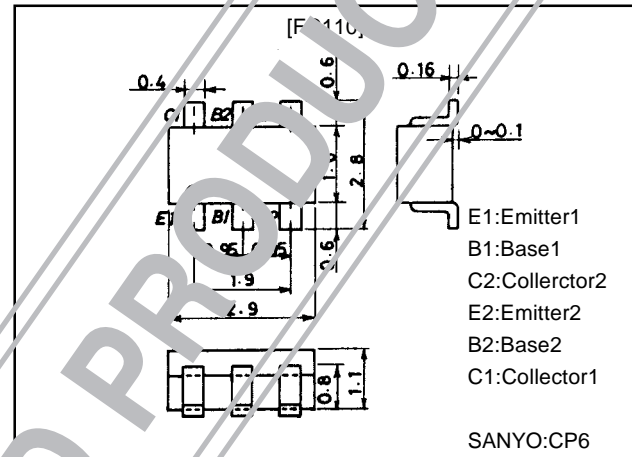
Switching Applications**Features**

- On-chip bias resistors (R1=22kΩ, R2=22kΩ)
- Composite type with 2 transistors contained in the CP package currently in use, improving the mounting efficiency greatly.
- The FC110 is formed with two chips, being equivalent to the 2SC3396, placed in one package.
- Excellent in thermal equilibrium and pair capability.

Electrical Connection**Package Dimensions**

unit:mm

2067

**Specifications****Absolute Maximum Ratings** at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CB0}		50	V
Collector-to-Emitter Voltage	V _{CEO}		50	V
Emitter-to-Base Voltage	V _{EB0}		10	V
Collector Current	I _C		100	mA
Collector Current (Pulse)	I _{CP}		200	mA
Collector Dissipation	P _C	unit	200	mW
Total Dissipation	P _T		300	mW
Junction Temperature	T _J		150	°C
Storage Temperature	T _S		-55 to+150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I _{CBO}	V _{CB} =40V, I _E =0			0.1	μA
Collector Cutoff Current	I _{CEO}	V _{CE} =40V, I _B =0			0.5	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =5V, I _C =0	70	113	160	μA
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =5mA	50			
Gain-Bandwidth Product	f _T	V _{CE} =10V, I _C =5mA		250		MHz
Output Capacitance	C _{ob}	V _{CB} =10V, f=1MHz		3.3		pF
C-E Saturation Voltage	V _{CE(sat)}	I _C =10mA, I _B =0.5mA		0.1	0.3	V
C-B Breakdown Voltage	V _{(BR)CBO}	I _C =10μA, I _E =0	50			V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C =100μA, R _{BE} =∞	50			V
Input OFF-State Voltage	V _{I(off)}	V _{CE} =5V, I _C =100μA	0.8	1.1	1.5	V
Input ON-State Voltage	V _{I(on)}	V _{CE} =0.2V, I _C =5mA	1.0	1.9	3.0	V
Input Resistance	R1		15	22	29	kΩ
Resistance Ratio	R1/R2		0.9	1.0	1.1	

Note: The specifications shown above are for each individual transistor.

Marking:110

SANYO Electric Co.,Ltd. Semiconductor Business Headquarters

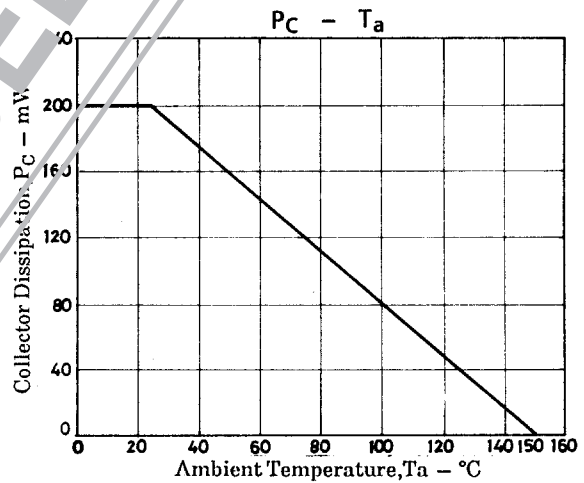
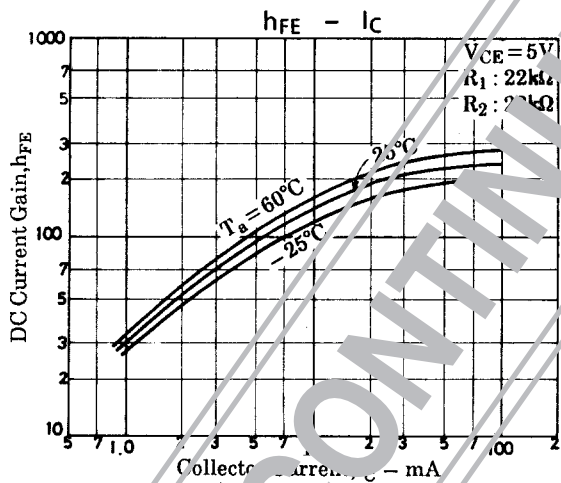
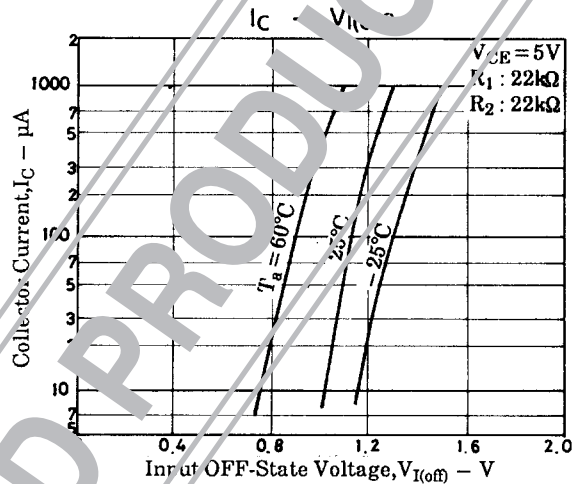
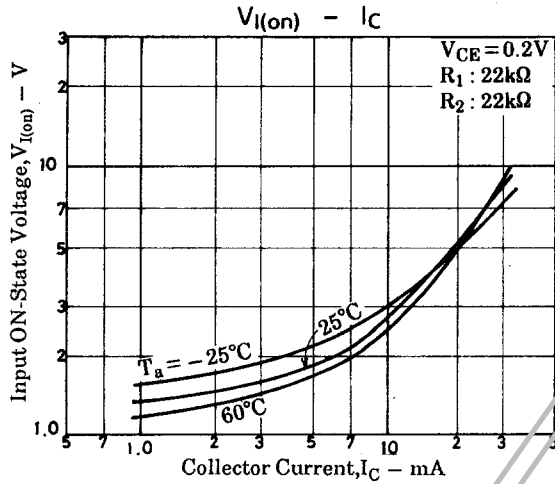
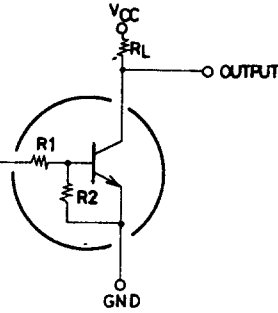
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

52098HA (KT)/4139MO, TS No.3078-1/2

Sample Application Circuit

Input ON-state voltage : 3V or greater

Input OFF-state voltage : 0.8V or less



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